

### 85V 140A N-Channel Enhancement Mode Power MOSFET

#### **General Description**

This Power MOSFET has been developed using advanced SGT process, which is specifically designed to minimize input capacitance and gate charge. This device is ideal for high-efficiency switching and synchronous rectification.

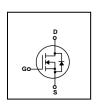
#### **FEATURES**

- RDSON $\leq$ 4.9m $\Omega$  @Vgs=10V, Id=50A
- Excellent RDS(ON) and Low Gate Charge

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· Lead free product is acquired

#### **SYMBOL**





#### **ASSEMBLY MESSAGE**

Product Name	Marking	Package	Packaging
BXS049N08P	BX049N08P	TO-220	Tube

#### **ABSOLUTE MAXIMUM RATINGS** (Tc=25°C unless otherwise noted)

Parameter		Symbol	Rating	Unit
		,	TO-220	
Drain-Source Voltage	Drain-Source Voltage		85	V
Drain Current Continuous (T <sub>C</sub> = 25°C)		I-	140	Α
Dialii Current	Continuous (T <sub>C</sub> = 100°C)	- I <sub>D</sub>	79	Α
Drain Current	Pulsed (Note1)	I <sub>DM</sub>	560	Α
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Power Dissipation T <sub>C</sub> =25°C		P <sub>D</sub>	189	W
Avalanche Energy Single Pulse		Eas	190	mJ
Maximum Junction Temperature		TJ	150	°C
Storage Temperature Range		T <sub>STG</sub>	-55 to 150	°C

Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature

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## THERMAL CHARACTERISTICS

Parameter	Max.		Unit	
Farameter	Symbol	TO-220	Onit	
Thermal Resistance, Junction-to-Case	Rejc	0.66	°C/W	

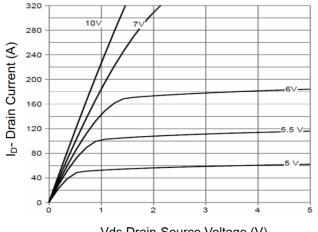
### **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub>=25°C,unless otherwise Noted)

Parameter	Symbol	Test Condition	Min.	Тур.	Max.	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	VGS=0V, ID=250µA	85	96		V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	VDS=85V, VGS=0V			1	uA
Gate-Body Leakage Current, Forward		VGS=20V			100	nA
Gate-Body Leakage Current, Reverse	I <sub>GSS</sub>	VGS=-20V			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	VDS=VGS, ID=250μA	2	3	4	V
Drain-Source On-State Resistance	Process	VGS=10V, ID=5A		3.8	4.9	mΩ
Diain-Source On-State Resistance	R <sub>DS(ON)</sub>	VGS=10V, ID=50A		4	4.9	mΩ
DYNAMIC PARAMETERS						
Input Capacitance	Cıss		-	4021	-	pF
Output Capacitance	Coss	VDS=40V, VGS=0V, f=1.0MHz	-	510	-	pF
Reverse Transfer Capacitance	Crss	1=1.0IVII 12	-	28	-	pF
SWITCHING PARAMETERS						
Turn-ON Delay Time	t <sub>D(ON)</sub>		-	20	-	ns
Turn-ON Rise Time	t <sub>R</sub>	VDD=40V, ID=60A, VGS =	-	60	-	ns
Turn-OFF Delay Time	t <sub>D(OFF)</sub>	10V, RG=1Ω	-	39	-	ns
Turn-OFF Fall-Time	t <sub>F</sub>		-	11	-	ns
Total Gate Charge(Note2)	$Q_{G}$	VDC 40V VCC 40V ID	-	72	-	nC
Gate Source Charge	Q <sub>GS</sub>	VDS =40V, VGS =10V, ID =60A	-	22	-	nC
Gate Drain Charge	Q <sub>GD</sub>	=00A	-	23	-	nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	IS=50A, VGS=0V	-		1.2	V
Diode Continuous Forward Current	Is		-		140	Α
Reverse Recovery Time	t <sub>RR</sub>	VGS = 0 V, I <sub>F</sub> = I <sub>S</sub>	-	65	-	nS
Reverse Recovery Charge	Q <sub>RR</sub>	di/dt=100 A/μs (Note4,5)	-	136	-	nC

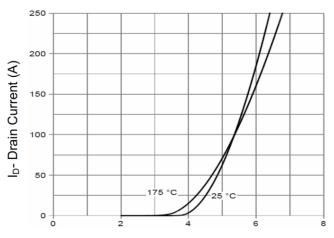
Note: 2. Essentially independent of operating temperature-



#### TYPICAL CHARACTERISTICS



Vds Drain-Source Voltage (V)



Vgs Gate-Source Voltage (V)

Figure 1 Output Characteristics

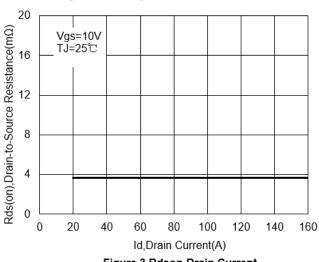
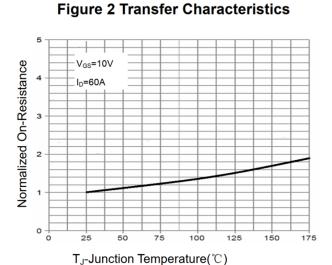


Figure 3.Rdson-Drain Current



**Figure 4 Rdson-Junction Temperature** 

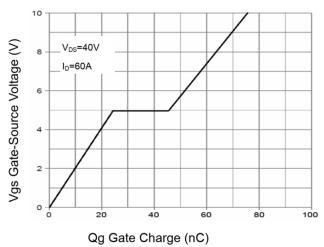
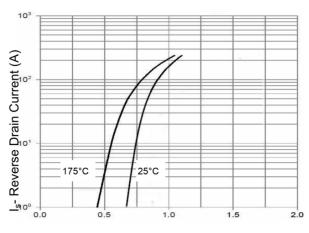


Figure 5 Gate Charge



Vsd Source-Drain Voltage (V)

Figure 6 Source- Drain Diode Forward



## **TYPICAL CHARACTERISTICS(Cont.)**

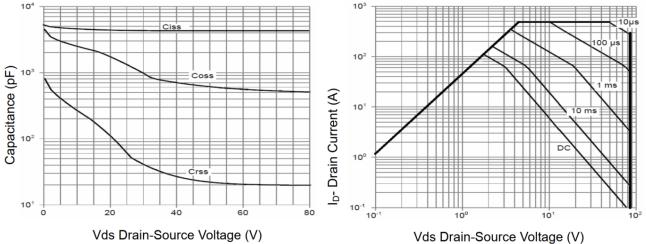


Figure 7 Capacitance vs Vds

Figure 8 Safe Operation Area

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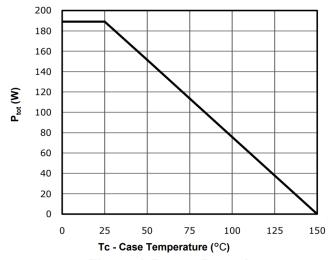
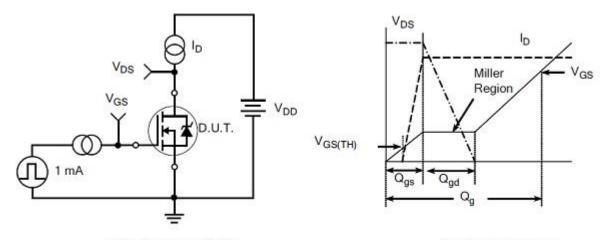


Figure 9 Power De-rating

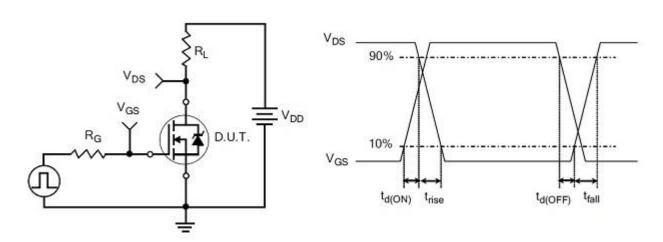


#### **TEST CIRCUITS AND WAVEFORMS**





Gate Charge Waveform



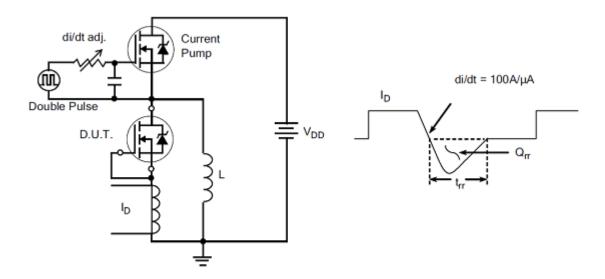
Resistive Switching Test Circuit

Resistive Switching Waveforms

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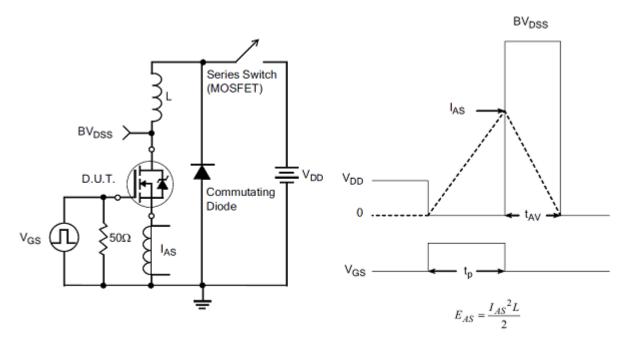


## **TEST CIRCUITS AND WAVEFORMS(Cont.)**



Diode Reverse Recovery Test Circuit

Diode Reverse Recovery Waveform



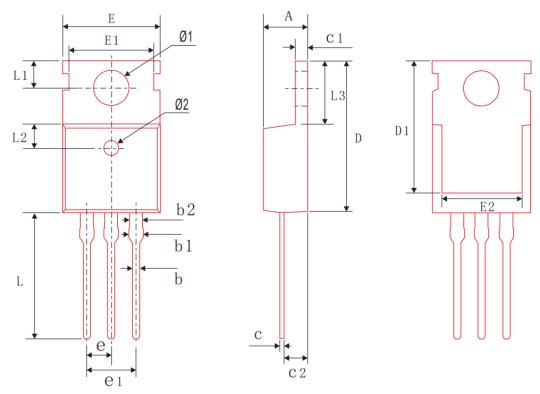
Unclamped Inductive Switching Test Circuit

Unclamped Inductive Switching Waveforms

Version: 1.0



# TO-220 Package



COMMON DIMENSIONS (UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	4. 30	4.50	4.70
b	0.70	0.80	0.90
b 1			1.42
b2	1. 17	1.27	1.37
С	0.40	0.50	0.60
C 1	1.25	1.30	1.35
C2	2.20	2.40	2.60
D	15. 45	15.65	15.85
D 1	13.20	13.40	13.60
Е	9.80	10.0	10.2
E1	8.60	8.70	8.80
E2	7.80	8.00	8.20
e 1	4.88	5. 08	5. 28
L	12.95	13. 15	13.35
L1	2.70	2.80	2.90
L2	2.40	2.50	2.60
L3	6.30	6.50	6.70
Ø1	3. 50	3.60	3.70
Ø2	1. 35	1.50	1.65
е		2.54BSC	

# **Revision history**

# **Document revision history**

Date	Revision	Changes
25-Oct-2020	1.0	First release

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